

**AMENDMENTS TO THE CLAIMS**

The following is a complete, marked-up listing of revised claims with a status identifier in parenthesis, underlined text indicating insertions, and strike through and/or double-bracketed text indicating deletions.

**LISTING OF CLAIMS**

1.-21. (Cancelled).

22. (Currently Amended) A capacitor of a semiconductor device, the capacitor comprising:

an interlayer dielectric (ILD) film on a semiconductor substrate, the ILD film including a conductive plug therein;

a lower electrode formed on the ILD film ~~a semiconductor substrate~~;

an AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film formed on the lower electrode;

an upper electrode formed on the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film; and

an oxidation barrier film formed between the lower electrode and the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film;

a dielectric film having a dielectric constant that is higher than that of the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film between the upper electrode and the AHO ((Al<sub>x</sub>,Hf<sub>1-x</sub>)O<sub>y</sub>) film,

wherein the dielectric film is an HfO<sub>2</sub> layer, a ZrO<sub>2</sub> layer, or an STO layer, ~~and~~

wherein the dielectric film is directly in contact with the upper electrode, and

wherein the lower electrode, the oxidation barrier film and the AHO film include a recess above the conductive plug, and the recess is filled by the upper electrode.

23.-37. (Cancelled).